

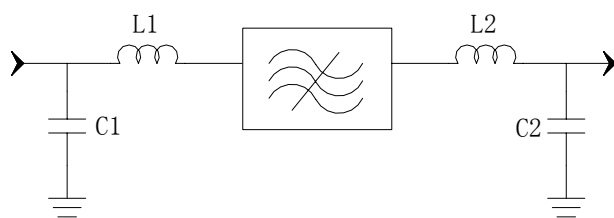
Specifications

Parameter	Unit	Minimum	Typical	Maximum
Center Frequency	MHz	114.9	115	115.1
Insertion Loss	dB		28.5	30
3 dB Bandwidth	MHz	4.1	4.16	
30 dB Bandwidth	MHz		4.8	4.9
40 dB Bandwidth	MHz		4.9	5.2
Passband Variation	dB		0.8	1
Group Delay Variation (80% of 3dB Bandwidth)	nsec		100	200
Absolute Delay	usec		3.88	4
Ultimate Rejection	dB	48	55	
Substrate Material		112LiTaO ₃		
Ambient Temperature	°C	25		
Package Size		DIP3512 (35.0x12.8x4.7mm ³)		

Notes:

1. All specifications are based on the test circuit shown
2. In production, devices will be tested at room temperature to a guardbanded specification to ensure electrical compliance over temperature
3. Electrical margin has been built into the design to account for the variations due to temperature drift and manufacturing tolerances
4. This is the optimum impedance in order to achieve the performance show


Matching Configuration



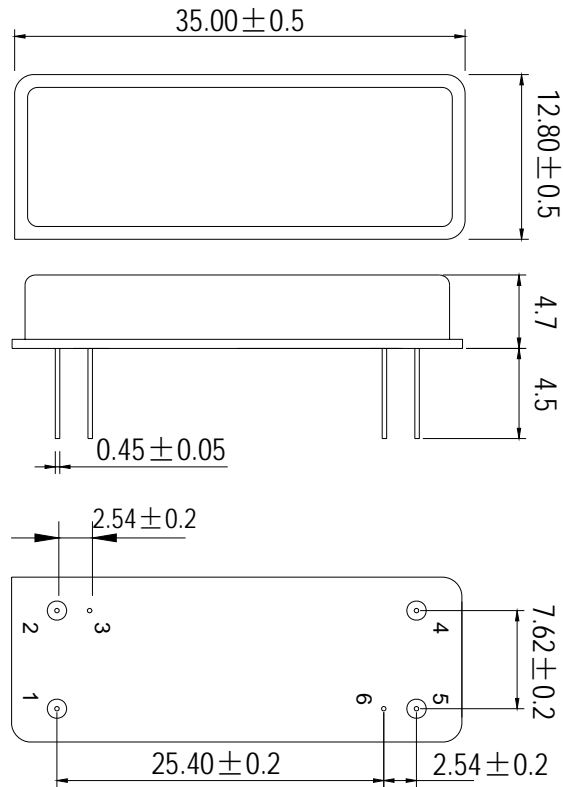
L1=39nH L2=56nH
C1=47pF C2=47pF

Source/Load Impedance=50 ohm

Notes - Component values may change depending
on board layout.

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Package Dimension

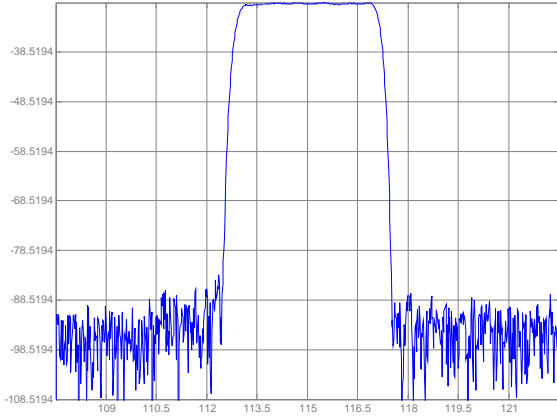


SIPAT Co., Ltd.
(CETC No. 26 Research Institute)
Nanping Huayuan Road No. 14
Chongqing, China, 400060

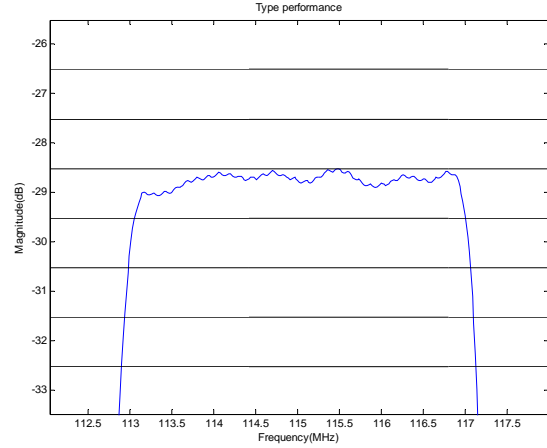
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Typical Performance

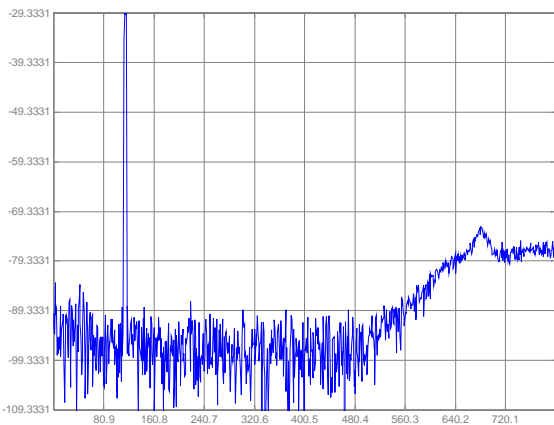
Frequency Respond



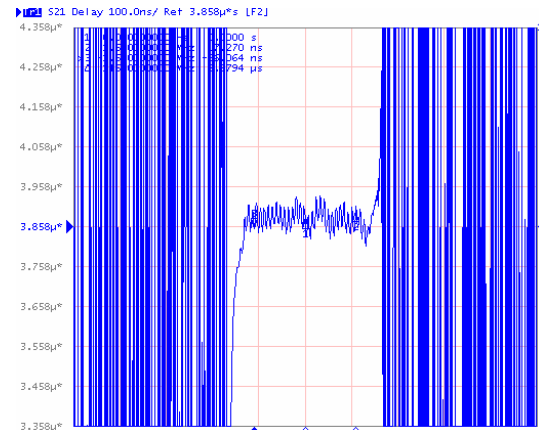
Passband Respond



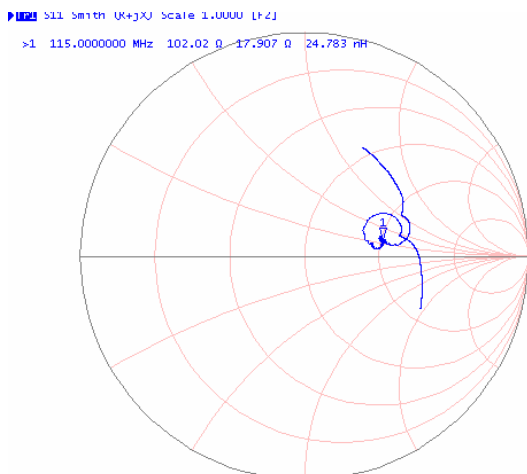
Wideband Respond



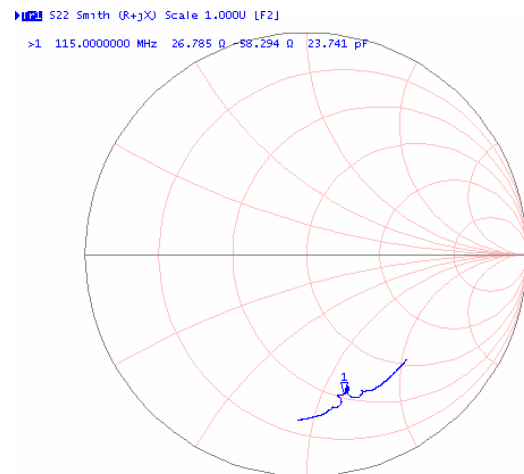
Group delay variation (80% of 3dB Bandwidth)



Simth Chart S11



Simth Chart S22



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